<u>Amendments to the Claims</u>:

This listing of claims replaces all prior versions and listings of claims in the application:

<u>Listing of Claims</u>:

Claims 1-18 (Canceled)

Claim 19 (Currently amended): A method of manufacturing a semiconductor device comprising:

forming a semiconductor film having a thickness between 150 and 1000 Å over a substrate;

emitting <u>a</u> pulse laser <u>light</u> **[[beams]]** at a rate of N <u>pulses</u> **[[beams]]** per second;

shaping the pulse laser <u>light</u> **[[beams]]** into <u>a beam</u> **[[beams]]** elongated in one direction at an irradiation surface through an optical system, the <u>beam</u> **[[beams]]** having a normal-distribution type energy profile of width L (m) perpendicular to the direction, <u>where L is larger than zero,</u> and the <u>beam</u> **[[beams]]** having substantially a constant energy distribution along the direction;

applying the <u>beam</u> **[[beams]]** to an arbitrarily selected portion of the semiconductor film; and

scanning the semiconductor film with the <u>beam</u> **[[beams]]** perpendicular to the direction at a speed V (m/s),

wherein the number of beams applied to the arbitrarily selected portion in one scan satisfies a relationship $3 \leq LN/V \leq 100$, and

wherein the width L (m) is defined as <u>a beam</u> **[[beams]]** in a region having 5% or more of an energy density with respect to a maximum energy density of the <u>beam</u> **[[beams]]** on the irradiation surface.

Claim 20 (Previously Presented): The method of claim 19 wherein the width is between 0.1 and 1 cm.

Claim 21 (Currently amended): The method of claim 19 wherein the beam **[[beams]]** along the direction has a length between 10 and 30 cm.

Claim 22 (Previously Presented): The method of claim 19 wherein the scanning step is conducted in air.

Claim 23 (Currently amended): A method of manufacturing a semiconductor device comprising:

forming a semiconductor film having a thickness between 150 and 1000 Å over a substrate;

emitting a pulse laser light **[[beams]]** at a rate of N pulses **[[beams]]** per second;

shaping the pulse laser light **[[beams]]** into a beam **[[beams]]** elongated in one direction at an irradiation surface through an optical system, the beam **[[beams]]** having a normal-distribution type energy profile of width L (m) perpendicular to the direction, where L is larger than zero, and the beam **[[beams]]** having substantially a constant energy distribution along the direction, and an average single-pulse energy density of the beam **[[beams]]** between 100 and 500 mJ/cm^2;

applying the beam **[[beams]]** to an arbitrarily selected portion of the semiconductor film; and

scanning the semiconductor film with the beam **[[beams]]** perpendicular to the direction at a speed V (m/s),

wherein the number of beams applied to the arbitrarily selected portion in one scan satisfies a relationship $3 \leq LN/V \leq 100$, and

wherein the width L (m) is defined as <u>a beam</u> **[[beams]]** in a region having 5% or more of an energy density with respect to a maximum energy density of the <u>beam</u> **[[beams]]** on the irradiation surface.

Claim 24 (Previously Presented): The method of claim 23 wherein the width is between 0.1 and 1 cm.

Claim 25 (Currently amended): The method of claim 23 wherein the <u>beam</u> **[[beams]]** along the direction has a length between 10 and 30 cm.

Claim 26 (Previously Presented): The method of claim 23 wherein the scanning step is conducted in air.

Claim 27 (Currently amended): A method of manufacturing a semiconductor device comprising:

forming a semiconductor film having a thickness between 150 and 1000 Å over a substrate;

emitting <u>a</u> pulse laser <u>light</u> **[[beams]]** at a rate of N <u>pulses</u> **[[beams]]** per second;

shaping the pulse laser <u>light</u> **[[beams]]** into <u>a beam</u> **[[beams]]** elongated in one direction at an irradiation surface through an optical system, the <u>beam</u> **[[beams]]** having a normal-distribution type energy profile of width L (m) perpendicular to the direction, <u>where L is larger than zero,</u> and the <u>beam</u> **[[beams]]** having substantially a constant energy distribution along the direction;

applying the <u>beam</u> **[[beams]]** to an arbitrarily selected portion of the semiconductor film; and

scanning the semiconductor film with the <u>beam</u> **[[beams]]** perpendicular to the direction at a speed V (m/s),

wherein the pulse laser comprises an excimer laser,

wherein the number of beams applied to the arbitrarily selected portion in one scan satisfies a relationship $3 \leq LN/V \leq 100$ **[[100]]**, and

wherein the width L (m) is defined as a beam **[[beams]]** in a region having 5% or more of an energy density with respect to a maximum energy density of the beam **[[beams]]** on the irradiation surface.

Claim 28 (Currently amended): The method of claim 27 wherein an average single-pulse energy density of the beam **[[beams]]** is between 100 and 500 mJ/cm^2.

Claim 29 (Previously Presented): The method of claim 27 wherein the width is between 0.1 and 1 cm.

Claim 30 (Currently amended): The method of claim 27 wherein the beam **[[beams]]** along the direction has a length between 10 and 30 cm.

Claim 31 (Previously Presented): The method of claim 27 wherein the scanning step is conducted in air.

Claim 32 (Currently amended): A method of manufacturing a semiconductor device comprising:

forming a semiconductor film having a thickness between 150 and 1000 Å over a substrate;

emitting a pulse laser light **[[beams]]** at a rate of N pulses **[[beams]]** per second;

shaping the pulse laser light **[[beams]]** into a beam **[[beams]]** elongated in one direction at an irradiation surface through an optical system, the beam **[[beams]]** having a trapezoidal energy profile of width L (m) perpendicular to the direction, where L is larger than zero, and the beam **[[beams]]** having substantially a constant energy distribution along the direction;

applying the beam **[[beams]]** to an arbitrarily selected portion of the semiconductor film; and

scanning the semiconductor film with the beam **[[beams]]** perpendicular to the direction at a speed V (m/s),

wherein the number of beams applied to the arbitrarily selected portion in one scan satisfies a relationship $3 \leq LN/V \leq 100$, and

wherein the width L (m) is defined as a beam **[[beams]]** in a region having 5% or more of an energy density with respect to a maximum energy density of the beam **[[beams]]** on the irradiation surface.

Claim 33 (Previously Presented): The method of claim 32 wherein the width is between 0.1 and 1 cm.

Claim 34 (Currently amended): The method of claim 32 wherein the beam **[[beams]]** along the direction has a length between 10 and 30 cm.

Claim 35 (Previously Presented): The method of claim 32 wherein the scanning step is conducted in air.

Claim 36 (Currently amended): A method of manufacturing a semiconductor device comprising:

forming a semiconductor film having a thickness between 150 and 1000 Å over a substrate;

emitting a pulse laser light **[[beams]]** at a rate of N pulses **[[times]]** per second;

shaping the pulse laser light **[[beams]]** into a beam **[[beams]]** elongated in one direction at an irradiation surface through an optical system, the beam **[[beams]]** having a trapezoidal energy profile of width L (m) perpendicular to the direction, where L is larger than zero, and the

beam **[[beams]]** having substantially a constant energy distribution along the direction, and an average single-pulse energy density of the beam **[[beams]]** between 100 and 500 mJ/cm^2;

applying the beam **[[beams]]** to an arbitrarily selected portion of the semiconductor film; and

scanning the semiconductor film with the beam **[[beams]]** perpendicular to the direction at a speed V (m/s),

wherein the number of beams applied to the arbitrarily selected portion in one scan satisfies a relationship $3 \leq LN/V \leq 100$, and

wherein the width L (m) is defined as beam **[[beams]]** in a region having 5% or more of an energy density with respect to a maximum energy density of the beam **[[beams]]** on the irradiation surface.

Claim 37 (Previously Presented): The method of claim 36 wherein the pulse laser comprises an excimer laser.

Claim 38 (Previously Presented): The method of claim 36 wherein the width is between 0.1 and 1 cm.

Claim 39 (Currently amended): The method of claim 36 wherein the beam **[[beams]]** along the direction has a length between 10 and 30 cm.

Claim 40 (Previously Presented): The method of claim 36 wherein the scanning step is conducted in air.

Claim 41 (Currently amended): A method of manufacturing a semiconductor device comprising:

forming a semiconductor film having a thickness between 150 and 1000 Å over a substrate;

emitting a pulse laser light **[[beams]]** at a rate of N pulses **[[beams]]** per second;

shaping the pulse laser light **[[beams]]** into a beam **[[beams]]** elongated in one direction at an irradiation surface through an optical system, the beam **[[beams]]** having a trapezoidal energy profile of width L (m) perpendicular to the direction, where L is larger than zero, and the beam **[[beams]]** having substantially a constant energy distribution along the direction;

applying the beam **[[beams]]** to an arbitrarily selected portion of the semiconductor film; and

scanning the semiconductor film with the beam **[[beams]]** perpendicular to the direction at a speed V (m/s),

wherein the pulse laser comprises an excimer laser,

wherein the number of beams applied to the arbitrarily selected portion in one scan satisfies a relationship $3 \leq LN/V \leq 100$, and

wherein the width L (m) is defined as a beam **[[beams]]** in a region having 5% or more of an energy density with respect to a maximum energy density of the beam **[[beams]]** on the irradiation surface.

Claim 42 (Previously Presented): The method of claim 41 wherein the width is between 0.1 and 1 cm.

Claim 43 (Currently amended): The method of claim 41 wherein the beam **[[beams]]** along the direction has a length between 10 and 30 cm.

Claim 44 (Previously Presented): The method of claim 41 wherein the scanning step is conducted in air.